

Smart High-Side Power Switch

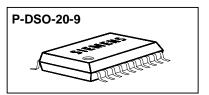
Two Channels: 2 x $60m\Omega$

Status Feedback

Product Summary

Operating Voltage	$V_{bb(on)}$	4.75.	41V
	Active channels	one	two parallel
On-state Resistance	R _{on}	$60 m\Omega$	$30 m\Omega$
Nominal load current	I _{L(NOM)}	4.0A	6.0A
Current limitation	$I_{L(SCr)}$	17A	17A

Package



General Description

- N channel vertical power MOSFET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology.
- Providing embedded protective functions

Applications

- μC compatible high-side power switch with diagnostic feedback for 5V, 12V and 24V grounded loads
- · All types of resistive, inductive and capacitve loads
- Most suitable for loads with high inrush currents, so as lamps
- · Replaces electromechanical relays, fuses and discrete circuits

Basic Functions

- Very low standby current
- CMOS compatible input
- Improved electromagnetic compatibility (EMC)
- Fast demagnetization of inductive loads
- Stable behaviour at undervoltage
- Wide operating voltage range
- Logic ground independent from load ground

Protection Functions

- Short circuit protection
- Overload protection
- Current limitation
- Thermal shutdown
- Overvoltage protection (including load dump) with external resistor
- Reverse battery protection with external resistor
- Loss of ground and loss of V_{bb} protection
- Electrostatic discharge protection (ESD)

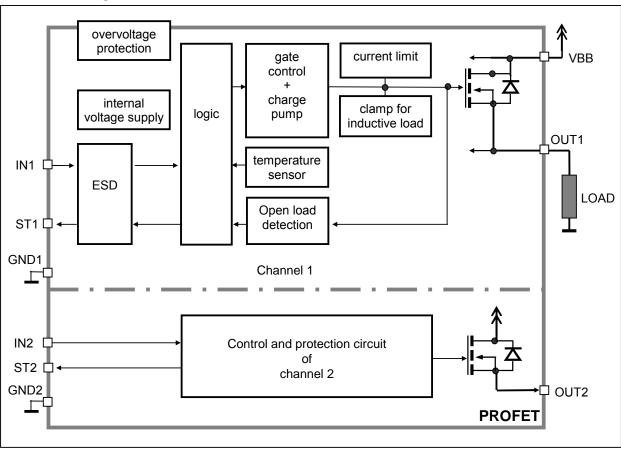
Diagnostic Function

- · Diagnostic feedback with open drain output
- Open load detection in ON-state
- · Feedback of thermal shutdown in ON-state

N1 Logic ST1 Channel IN2 Logic Channel ST2 Channel PROFET GND Load 2



Functional diagram



Pin Definitions and Functions

Pin	Symbol	Function
1,10,	V_{bb}	Positive power supply voltage. Design the
11,12,		wiring for the simultaneous max. short circuit
15,16,		currents from channel 1 to 2 and also for low
19,20		thermal resistance
3	IN1	Input 1,2, activates channel 1,2 in case of
7	IN2	logic high signal
17,18	OUT1	Output 1,2, protected high-side power output
13,14	OUT2	of channel 1,2. Design the wiring for the max.
		short circuit current
4	ST1	Diagnostic feedback 1,2 of channel 1,2,
8	ST2	open drain, low on failure
2	GND1	Ground 1 of chip 1 (channel 1)
6	GND2	Ground 2 of chip 2 (channel 2)
5,9	N.C.	Not Connected

Pin configuration

(top view)		
V_{bb}	1 •	20	V_{bb}
GND1	2	19	V _{bb}
IN1	3	18	OUT1
ST1	4	17	OUT1
N.C.	5	16	V_{bb}
GND2	6	15	V_{bb}
IN2	7	14	OUT2
ST2	8	13	OUT2
N.C.	9	12	V_{bb}
V_{bb}	10	11	V_{bb}



Maximum Ratings at $T_i = 25$ °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	$V_{\rm bb}$	43	V
Supply voltage for full short circuit protection $T_{j,\text{start}} = -40 \dots + 150 ^{\circ}\text{C}$	V _{bb}	24	V
Load current (Short-circuit current, see page 5)	<i>I</i> ∟	self-limited	Α
Load dump protection ¹⁾ $V_{\text{LoadDump}} = V_{\text{A}} + V_{\text{S}}$, $V_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}}^{(2)} = 2 \Omega$, $t_{\text{d}} = 200 \text{ ms}$; IN = low or high, each channel loaded with $R_{\text{L}} = 8.0 \Omega$,	V _{Load dump} ³⁾	60	V
Operating temperature range	T _j	-40+150	°C
Storage temperature range	$T_{ m stg}$	-55+150	
Power dissipation (DC) ⁴⁾ $T_a = 25$ °C:	P _{tot}	3.7	W
(all channels active) $T_a = 85$ °C:		1.9	
Maximal switchable inductance, single pulse $V_{bb} = 12V$, $T_{j,start} = 150^{\circ}C^{4}$,			
$I_L = 4.0 \text{ A}, E_{AS} = 220 \text{ mJ}, 0\Omega$ one channel:	Z_{L}	19.9	mH
$I_L = 6.0 \text{ A}$, $E_{AS} = 540 \text{ mJ}$, 0Ω two parallel channels:		22.3	
see diagrams on page 9			
Electrostatic discharge capability (ESD) IN: (Human Body Model) ST: out to all other pins shorted: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993	V _{ESD}	1.0 4.0 8.0	kV
R=1.5kΩ; C=100pF		4040	
Input voltage (DC)	$V_{\rm IN}$	-10 +16	V
Current through input pin (DC)	/ _{IN}	±2.0	mA
Current through status pin (DC)	I _{ST}	±5.0	
see internal circuit diagram page 8			

Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
			min	typ	Max	
Thermal resistance		_			40.5	1.7.0.0.1
junction - soldering point ^{4),5)}	each channel:	R_{thjs}			13.5	K/W
junction - ambient ⁴⁾	one channel active:	R_{thja}		41		
	all channels active:			34		

Supply voltages higher than V_{bb(AZ)} require an external current limit for the GND and status pins (a 150Ω resistor for the GND connection is recommended.

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²⁾ $R_{\rm I}$ = internal resistance of the load dump test pulse generator

³⁾ V_{Load dump} is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 14

⁵⁾ Soldering point: upper side of solder edge of device pin 15. See page 14



Electrical Characteristics

Parameter and Conditions, each of the two channels at $T_j = -40+150$ °C, $V_{bb} = 12$ V unless otherwise specified		Symbol		Values		Unit	
			min	typ	Max		
Load Switching Capabilities a	nd Cha	racteristics					
On-state resistance (V _{bb} to OU	T); IL = 2	A, $V_{bb} \ge 7V$					
each cha	ınnel,	$T_{\rm j} = 25^{\circ}{\rm C}$:	Ron		50	60	mΩ
		$T_{\rm j} = 150^{\circ}{\rm C}$:			100	120	
two parallel chasee diagram, page 10	annels,	$T_{\rm j} = 25^{\circ}{\rm C}$:			25	30	
Nominal load current	one char	nnel active:	I _{L(NOM)}	3.6	4.0		Α
two parall	lel chanı	nels active:		5.5	6.0		
Device on PCB ⁶), $T_a = 85$ °C, $T_j \le 15$	50°C						
Output current while GND discontinuous Vbb = 30 V, VIN = 0, see diagram pa		r pulled up ⁷⁾ ;	I _{L(GNDhigh)}			2	mA
Turn-on time ⁸⁾ IN	to	90% V _{OUT} :	<i>t</i> on	30	100	200	μs
Turn-off time IN $R_{\rm L} = 12 \Omega$	¬∟ to	10% V _{OUT} :	$t_{ m off}$	30	100	200	
Slew rate on 8) 10 to 30% V_{OUT} , $R_L = 12 \Omega$	$T_{\rm j} = 25^{\circ}$	T _j = -40°C: °C150°C:	d V/dt _{on}	0.15 0.15		1 0.8	V/µs
Slew rate off 8) 70 to 40% V_{OUT} , $R_L = 12 \Omega$	$T_{\rm j} = 25^{\circ}$	<i>T</i> _j = -40°C: °C150°C:	-d V/dt _{off}	0.15 0.15		1 0.8	V/µs
Operating Parameters							
Operating voltage		Tj=-40	V _{bb(on)}	4.75		41	V
	$T_i=2$	25150°C:	,			43	
Overvoltage protection ⁹⁾	,	<i>T</i> _i =-40°C:	$V_{\rm bb(AZ)}$	41			V
$I_{bb} = 40 \text{ mA}$	$T_{\rm i} = 2$	25150°C:	,	43	47	52	
Standby current ¹⁰⁾	$T_{\rm j} = -40$	0°C25°C:	I _{bb(off)}		10	18	μΑ
$V_{IN} = 0$; see diagram page 10	•	$T_{\rm j}$ =150°C:	, ,			50	
Leakage output current (include	ed in I _{bb(c}	off))	I _{L(off)}		1	10	μΑ
Vin = 0	•						
Operating current ¹¹⁾ , $V_{IN} = 5V$,							
$I_{\text{GND}} = I_{\text{GND1}} + I_{\text{GND2}},$		channel on:	I _{GND}		0.8 1.6	1.5 3.0	mA
	two ch	nannels on:			1.0	5.0	

⁶⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 14

⁷⁾ not subject to production test, specified by design

⁸⁾ See timing diagram on page 11.

Supply voltages higher than V_{bb(AZ)} require an external current limit for the GND and status pins (a 150Ω resistor for the GND connection is recommended). See also V_{ON(CL)} in table of protection functions and circuit diagram on page 8.

¹⁰⁾ Measured with load; for the whole device; all channels off

¹¹⁾ Add I_{ST} , if $I_{ST} > 0$



Parameter and Conditions, each o	Symbol		Values			
at $T_j = -40+150$ °C, $V_{bb} = 12$ V unless oth	erwise specified		min	typ	Max	
Protection Functions ¹²⁾						
Current limit, (see timing diagrams, page	je 12)					
	<i>T</i> _j =-40°C:	$I_{L(lim)}$	21	28	36	Α
	<i>T</i> _j =25°C:		17	22	31	
	$T_{j} = +150^{\circ}C$:		12	16	24	
Repetitive short circuit current limit,						
$T_{j} = T_{jt}$	each channel	I _{L(SCr)}		17		Α
two p	arallel channels	, ,		17		
(see timing diagrams, page 12)						
Initial short circuit shutdown time	$T_{\rm j,start}$ =25°C:	t _{off(SC)}		2.4		ms
(see timing dia	grams on page 12)					
Output clamp (inductive load switch						V
at $VON(CL) = V_{bb} - VOUT$, $I_{L} = 40 \text{ mA}$	$T_{\rm j}$ =-40°C:	$V_{ON(CL)}$	41			
	=25°C150°C:		43	47	52	
Thermal overload trip temperature		T_{jt}	150			°C
Thermal hysteresis		$\Delta T_{\rm jt}$		10		K
Reverse Battery						
Reverse battery voltage 14)		- V _{bb}			32	V
Drain-source diode voltage ($V_{out} > V_{out} > V_{out$	bb)	-V _{ON}		600		mV

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¹²⁾ Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

¹³⁾ If channels are connected in parallel, output clamp is usually accomplished by the channel with the lowest VON(CL)

Requires a 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 3 and circuit page 8).



Parameter and Conditions, eac	Symbol		Values		Unit	
at $T_j = -40+150$ °C, $V_{bb} = 12 \text{ V unless}$	otherwise specified		min	typ	Max	
		1				I.
Diagnostic Characteristics						
Open load detection current, (on-	condition)					
	each channel	I _{L (OL)}	10		500	mA
Investigated Officer Foodback (15)						
Input and Status Feedback ¹⁵⁾		T 5		0 = 1		1.0
Input resistance (see circuit page 8)		R_{I}	2.5	3.5	6	kΩ
Input turn-on threshold voltage	V _{IN(T+)}	1.7		3.2	V	
Input turn-off threshold voltage	$V_{\text{IN(T-)}}$	1.5			V	
		` ,	1.5	0.5		V
Input threshold hysteresis	1/ 0.41/	$\Delta V_{\rm IN(T)}$				
Off state input current	$V_{IN} = 0.4 \text{ V}$:	I _{IN(off)}	1		50	μΑ
On state input current	$V_{IN} = 5 \text{ V}$:	I _{N(on)}	20	50	90	μΑ
Delay time for status with open looff; (see diagram on page 13)	oad after switch	$t_{ m d(ST~OL4)}$	100	520	900	μs
Status invalid after positive input	slope	$t_{d(ST)}$			500	μs
(open load)		, ,				
Status output (open drain)						
Zener limit voltage	$I_{ST} = +1.6 \text{ mA}$:	V _{ST(high)}	5.4	6.1		V
ST low voltage	$I_{ST} = +1.6 \text{ mA}$:	$V_{\rm ST(low)}$			0.4	

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 $^{^{\}rm 15)}$ If ground resistors $\rm R_{\rm GND}$ are used, add the voltage drop across these resistors.



Truth Table

Channel 1	Input 1	Output 1	Status 1
Channel 2	Input 2	Output 2	Status 2
	level	level	BTS 728L2
Normal	L	L	Н
operation	Н	Н	Н
Open load	L	Z	Н
	Н	Н	L
Overtem-	L	L	Н
perature	Н	L	L

L = "Low" Level

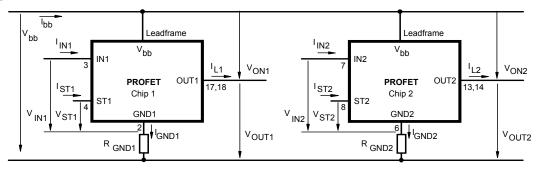
X = don't care

Z = high impedance, potential depends on external circuit

H = "High" Level Status signal valid after the time delay shown in the timing diagrams

Parallel switching of channel 1 and 2 is easily possible by connecting the inputs and outputs in parallel. The status outputs ST1 and ST2 have to be configured as a 'Wired OR' function with a single pull-up resistor.

Terms

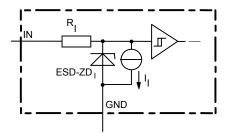


Leadframe (V_{bb}) is connected to pin 1,10,11,12,15,16,19,20

External R_{GND} optional; two resistors R_{GND1}, R_{GND2} = 150 Ω or a single resistor R_{GND} = 75 Ω for reverse battery protection up to the max. operating voltage.

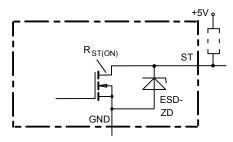


Input circuit (ESD protection), IN1 or IN2



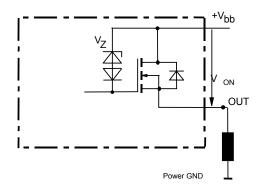
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Status output, ST1 or ST2



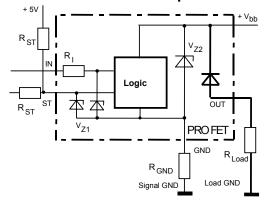
ESD-Zener diode: 6.1 V typ., max 5.0 mA; R_{ST(ON)} < 375 Ω at 1.6 mA. The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Inductive and overvoltage output clamp, OUT1 or OUT2



VON clamped to VON(CL) = 47 V typ.

Overvolt. and reverse batt. protection

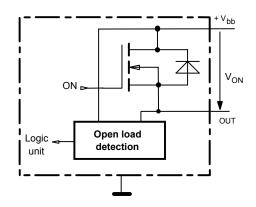


 V_{Z1} = 6.1 V typ., V_{Z2} = 47 V typ., R_{GND} = 150 Ω, R_{ST} = 15 kΩ, R_{I} = 3.5 kΩ typ.

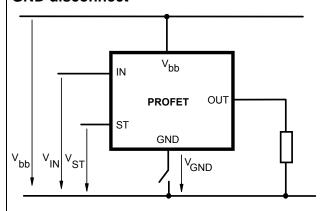
In case of reverse battery the load current has to be limited by the load. Temperature protection is not active

Open-load detection OUT1 or OUT2

ON-state diagnostic Open load, if $V_{\rm ON}$ < R_{ON} • I_{L(OL)}; IN high



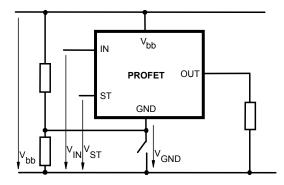
GND disconnect



Any kind of load. In case of IN = high is $V_{OUT} \approx V_{IN} - V_{IN(T+)}$. Due to $V_{GND} > 0$, no $V_{ST} =$ low signal available.

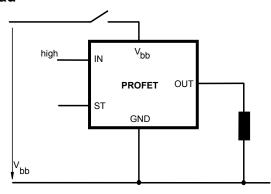


GND disconnect with GND pull up



Any kind of load. If $V_{GND} > V_{IN} - V_{IN(T+)}$ device stays off Due to $V_{GND} > 0$, no $V_{ST} = low$ signal available.

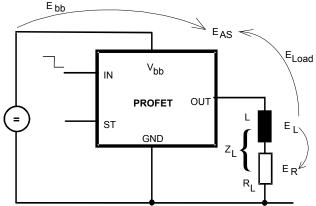
V_{bb} disconnect with energized inductive load



For inductive load currents up to the limits defined by $Z_{\scriptscriptstyle L}$ (max. ratings and diagram on page 9) each switch is protected against loss of V_{bb} .

Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load all the load current flows through the GND connection.

Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_{L} = \frac{1}{2} \cdot L \cdot I_{L}^{2}$$

While demagnetizing load inductance, the energy dissipated in PROFET is

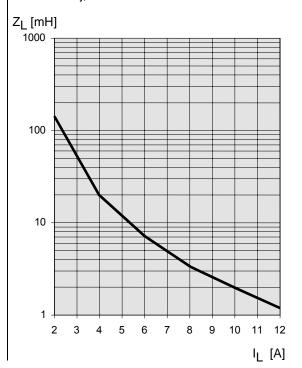
$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} \cdot i_L(t) dt$$

with an approximate solution for $R_L > 0 \Omega$:

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L} (V_{bb} + |V_{OUT(CL)}|) ln (1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|})$$

Maximum allowable load inductance for a single switch off (one channel)⁴⁾

$$L = f(I_L)$$
; $T_{i,start} = 150$ °C, $V_{bb} = 12$ V, $R_L = 0$ Ω





0

3

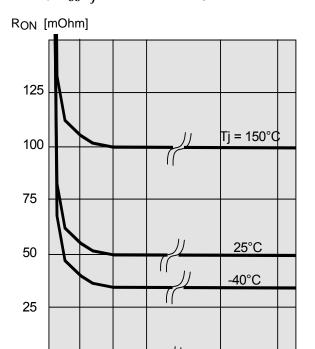
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7

9

Typ. on-state resistance

 $R_{ON} = f(V_{bb}, T_j)$; $I_L = 2 \text{ A}$, $I_N = \text{high}$

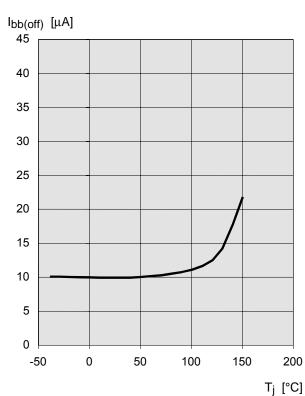


30

40 V_{bb} [V]

Typ. standby current

 $I_{bb(off)} = f(T_j); V_{bb} = 9...34 \text{ V}, IN1,2 = low$





Timing diagrams

Both channels are symmetric and consequently the diagrams are valid for channel 1 and channel 2

Figure 1a: V_{bb} turn on:

IN1

IN2

Vout1

Vout2

ST1 open drain

AST2 open drain

t

Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition:

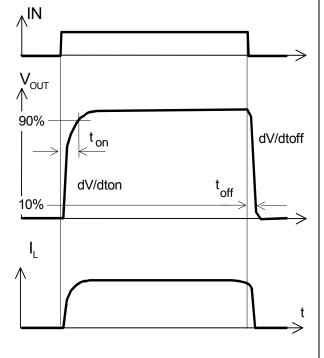
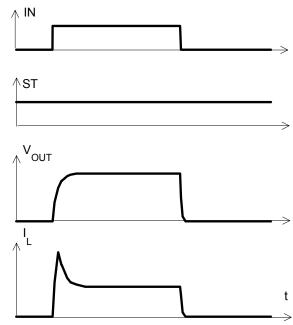
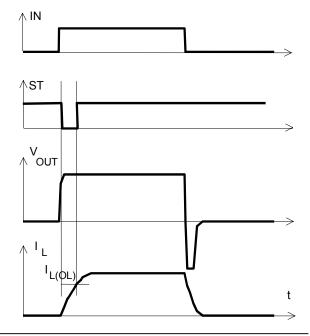


Figure 2b: Switching a lamp:



The initial peak current should be limited by the lamp and not by the current limit of the device.

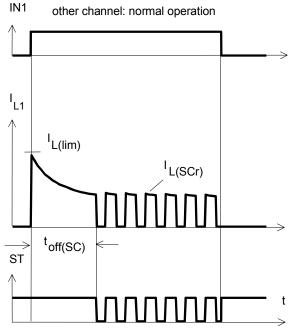
Figure 2c: Switching an inductive load





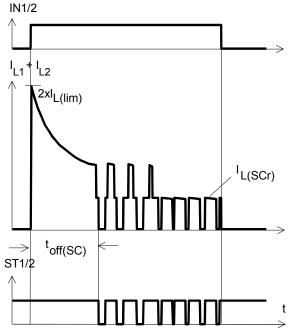
*) if the time constant of load is too large, open-load-status may occur

Figure 3a: Turn on into short circuit: shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions

Figure 3b: Turn on into short circuit: shut down by overtemperature, restart by cooling (two parallel switched channels 1 and 2)



ST1 and ST2 have to be configured as a 'Wired OR' function ST1/2 with a single pull-up resistor.

Figure 4a: Overtemperature: Reset if $T_i < T_{it}$

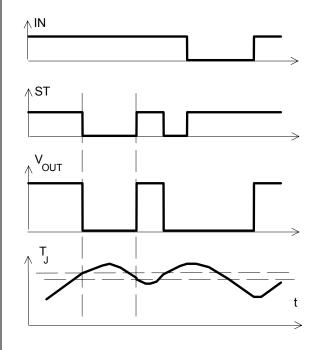


Figure 5a: Open load: detection in ON-state, open load occurs in on-state

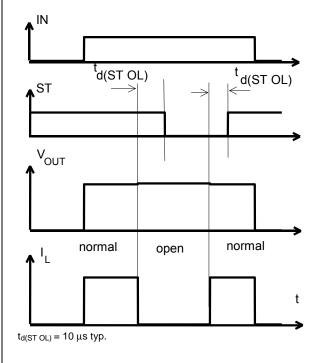
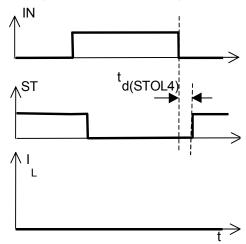




Figure 5b: Open load: turn on/off to open load

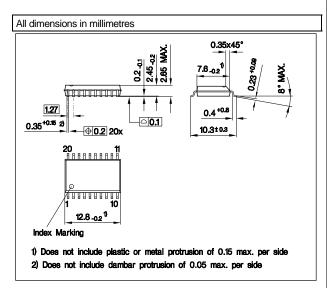




Package and Ordering Code

Standard: P-DSO-20-9

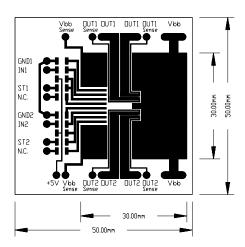
Sales Code	BTS 728 L2
Ordering Code	Q67060-S7014-A2



Definition of soldering point with temperature T_s : upper side of solder edge of device pin 15.



Printed circuit board (FR4, 1.5mm thick, one layer $70\mu m$, $6cm^2$ active heatsink area) as a reference for max. power dissipation P_{tot} , nominal load current $I_{L(NOM)}$ and thermal resistance R_{thia}



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